

DSA120X200LB

preliminary

Schottky Diode Gen ²	
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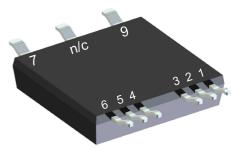
 $V_{RRM} = 200 V$ $I_{FAV} = 2x 65 A$ $V_{F} = 0.82 V$

High Performance Schottky Diode Low Loss and Soft Recovery Parallel legs

Part number

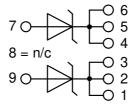
DSA120X200LB

Marking on Product: DSA120X200LB



Backside: isolated





Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operationLow voltage peaks for reduced
- protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: SMPD

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

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IXYS reserves the right to change limits, conditions and dimensions.



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Schottky							
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse block	ng voltage	$T_{vJ} = 25^{\circ}C$			200	V
V _{RRM}	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I _R	reverse current, drain current	$V_{R} = 200 V$	$T_{VJ} = 25^{\circ}C$			1	mA
		$V_{R} = 200 V$	$T_{vJ} = 125^{\circ}C$			5	mA
V _F	forward voltage drop	I _F = 60 A	$T_{vJ} = 25^{\circ}C$			0.98	V
		I _F = 120 A				1.22	V
		$I_{F} = 60 \text{ A}$	T _{vJ} = 150°C			0.82	V
		$I_{F} = 120 \text{ A}$				1.10	V
FAV	average forward current	T _c = 130°C	T _{vJ} = 175°C			65	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage $T_{v_1} = 175^{\circ}$		T _{vJ} = 175°C			0.51	V
r _F	slope resistance } for power lo	oss calculation only				2.7	mΩ
R _{thJC}	thermal resistance junction to cas	е				0.8	K/W
R _{thCH}	thermal resistance case to heatsir	nk			0.40		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			185	W
	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_{R} = 0 V$	$T_{vJ} = 45^{\circ}C$			700	Α
C	junction capacitance	$V_{R} = 24 V f = 1 MHz$	$T_{vJ} = 25^{\circ}C$		394		pF

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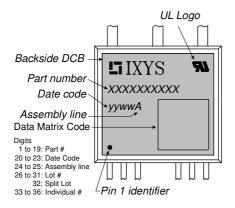
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Package SMPD					Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal				100	Α	
T _{vj}	virtual junction temperature			-55		175	°C	
T _{op}	operation temperature			-55		150	°C	
T _{stg}	storage temperature			-55		150	°C	
Weight					8.5		g	
F _c	mounting force with clip			40		130	Ν	
d _{Spp/App}	creepage distance on surface striking distance through air		1.6			mm		
d _{Spb/Apb}	creepage ustance on surface	Striking distance through an	terminal to backside	4.0			mm	
V	isolation voltage	t = 1 second		3000			V	
	t = 1 minute		50/60 Hz, RMS; liso∟ ≤ 1 mA	2500			V	



Part description

- D = Diode
- S = Schottky Diode A = Iow VF
- 120 = Current Rating [A]
- X = Parallel legs
- 200 = Reverse Voltage [V]
- LB = SMPD-B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA120X200LB-TUB	DSA120X200LB	Tube	20	524773
Alternative	DSA120X200LB-TRR	DSA120X200LB	Tape & Reel	200	523115

Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 175 ^{\circ}C$
)[R	Schottky		
V _{0 max}	threshold voltage	0.51		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	2.7		mΩ

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